

Silicon PNP Power Transistors

2SA1726

DESCRIPTION

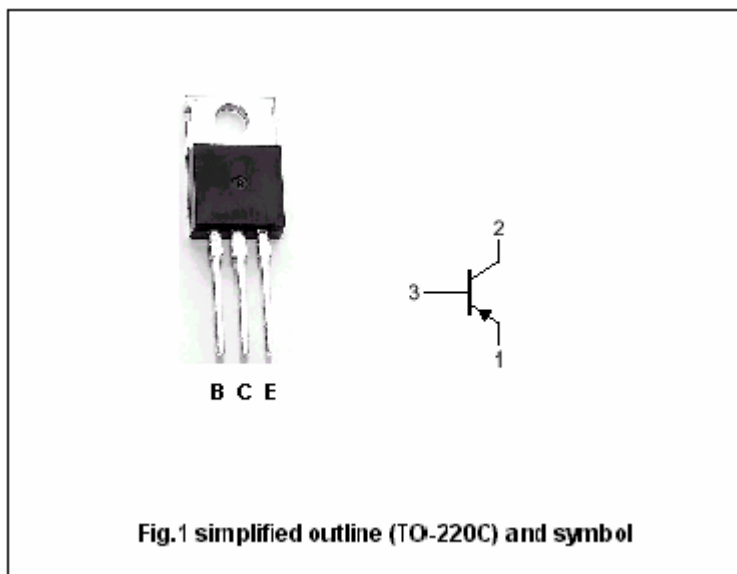
- With TO-220C package
- Complement to type 2SC4512

APPLICATIONS

- Audio and General Purpose

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-6	A
I_B	Base current		-3	A
P_C	Collector dissipation	$T_C=25^\circ\text{C}$	50	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-25mA$; $R_{BE}=\infty$	-80			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=-2A$; $I_B=-0.2A$			-0.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-80V$; $I_E=0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-6V$; $I_C=0$			-10	μA
h_{FE}	DC current gain	$I_C=-2A$; $V_{CE}=-4V$	50		180	
C_{OB}	Collector output capacitance	$f=1MHz$; $V_{CB}=-10V$		150		pF
f_T	Transition frequency	$I_E=0.5A$; $V_{CE}=-12V$		20		MHz

Switching times

t_{on}	Turn-on time	$V_{CC}=-30V$; $I_C=-3A$ $I_{B1}=-I_{B2}=-0.3A$ $R_L=10\Omega$		0.18		μs
t_{stg}	Storage time			1.10		μs
t_f	Fall time			0.21		μs

◆ h_{FE} Classifications

O	P	Y
50-100	70-140	90-180

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PACKAGE OUTLINE



Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)

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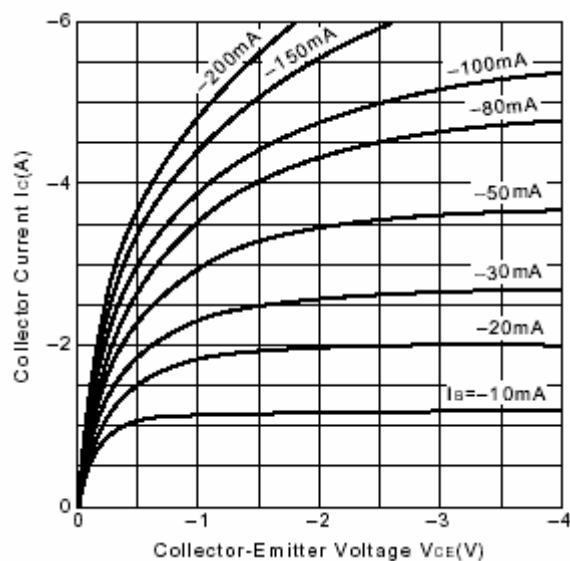


Fig.3 Static Characteristic

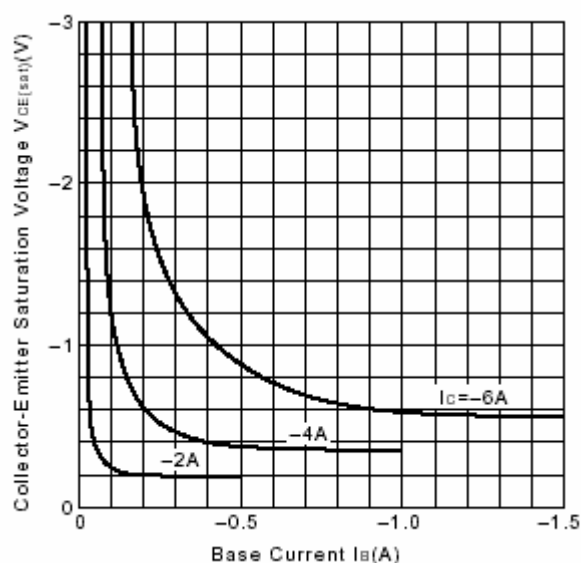
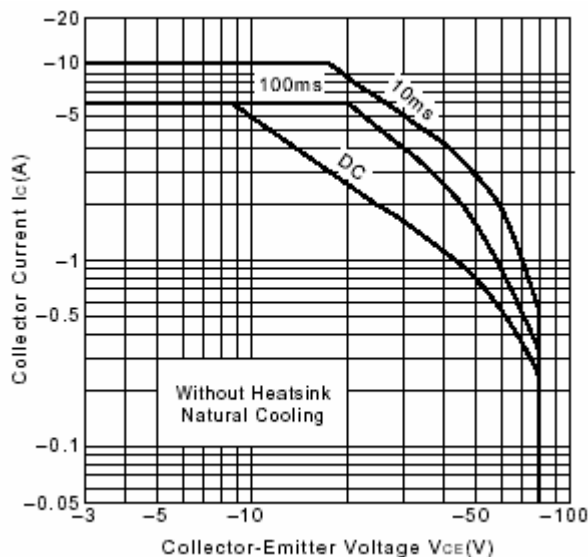
Fig.4 $V_{CE(sat)} - I_B$ Characteristics

Fig.5 Safe Operating Area

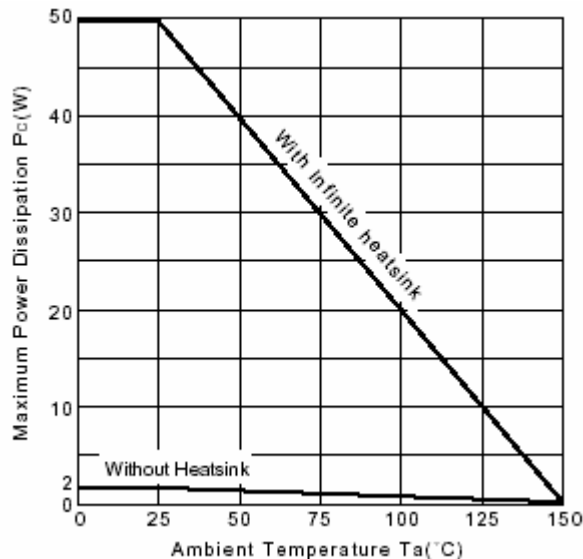
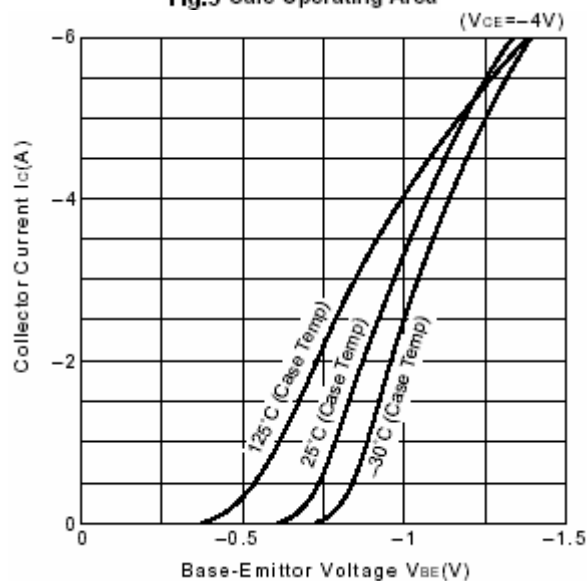
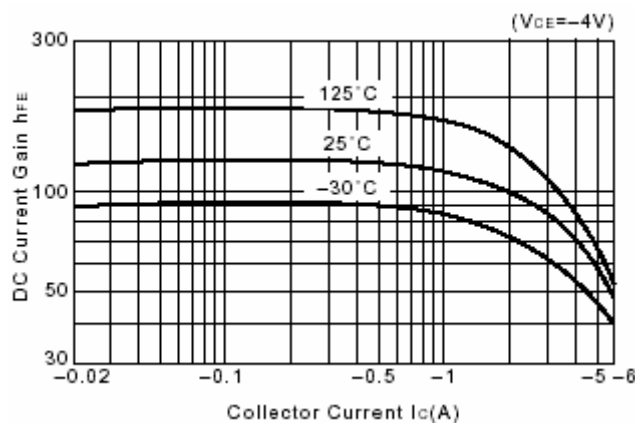
Fig.6 $P_C - T_a$ DeratingFig.7 $I_C - V_{BE}$ 

Fig.8 DC current Gain